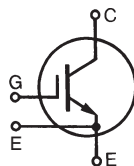


# 600V XPT™ IGBT

## GenX3™

# IXYN150N60B3

Extreme Light Punch through  
IGBT for 10-30kHz Switching

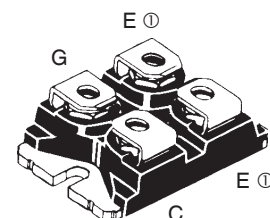


$$\begin{aligned} V_{CES} &= 600V \\ I_{C110} &= 140A \\ V_{CE(sat)} &\leq 2.20V \\ t_{fi(typ)} &= 80ns \end{aligned}$$

Symbol	Test Conditions	Maximum Ratings	
$V_{CES}$	$T_J = 25^\circ\text{C to } 175^\circ\text{C}$	600	V
$V_{CGR}$	$T_J = 25^\circ\text{C to } 175^\circ\text{C}, R_{GE} = 1M\Omega$	600	V
$V_{GES}$	Continuous	$\pm 20$	V
$V_{GEM}$	Transient	$\pm 30$	V
$I_{C25}$	$T_C = 25^\circ\text{C}$ (Chip Capability)	250	A
$I_{LRMS}$	Terminal Current Limit	200	A
$I_{C110}$	$T_C = 110^\circ\text{C}$	140	A
$I_{CM}$	$T_C = 25^\circ\text{C}, 1\text{ms}$	750	A
$I_A$	$T_C = 25^\circ\text{C}$	75	A
$E_{AS}$	$T_C = 25^\circ\text{C}$	1	J
<b>SSOA</b> <b>(RBSOA)</b>	$V_{GE} = 15V, T_{VJ} = 150^\circ\text{C}, R_G = 2\Omega$ Clamped Inductive Load	$I_{CM} = 300$ $V_{CE} \leq V_{CES}$	A
$t_{sc}$ <b>(SCSOA)</b>	$V_{GE} = 15V, V_{CE} = 360V, T_J = 150^\circ\text{C}$ $R_G = 82\Omega$ , Non Repetitive	8	$\mu\text{s}$
$P_C$	$T_C = 25^\circ\text{C}$	830	W
$T_J$		-55 ... +175	$^\circ\text{C}$
$T_{JM}$		175	$^\circ\text{C}$
$T_{stg}$		-55 ... +175	$^\circ\text{C}$
$V_{ISOL}$	50/60Hz $I_{ISOL} \leq 1\text{mA}$	$t = 1\text{min}$ $t = 1\text{s}$	2500 3000 V~ V~
$M_d$	Mounting Torque Terminal Connection Torque	1.5/13 1.3/11.5	Nm/lb.in Nm/lb.in
<b>Weight</b>		30	g

SOT-227B, miniBLOC

 E153432



G = Gate, C = Collector, E = Emitter  
Ⓢ either emitter terminal can be used as  
Main or Kelvin Emitter

### Features

- Optimized for Low Conduction and Switching Losses
- miniBLOC, with Aluminium Nitride Isolation
- International Standard Package
- Isolation Voltage 2500V~
- Optimized for 10-30kHz Switching
- Square RBSOA
- Avalanche Rated
- Short Circuit Capability
- High Current Handling Capability

### Advantages

- High Power Density
- Low Gate Drive Requirement

### Applications

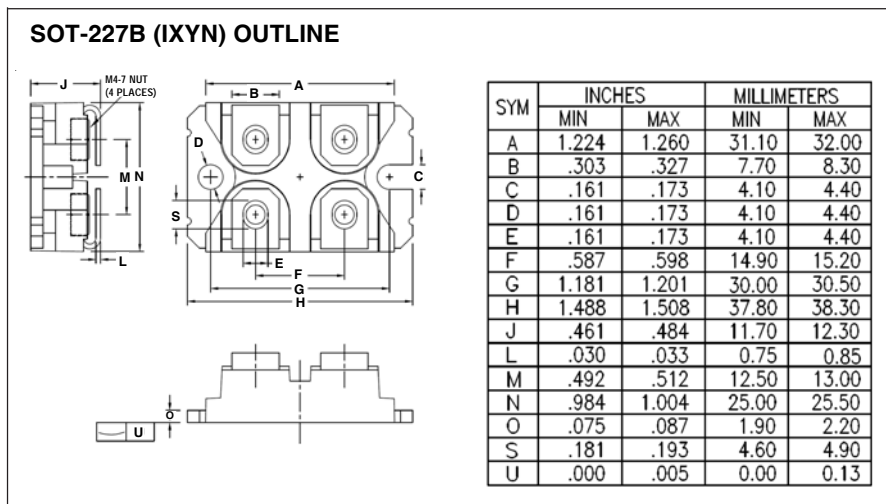
- Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Battery Chargers
- Welding Machines
- Lamp Ballasts

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$BV_{CES}$	$I_C = 250\mu\text{A}, V_{GE} = 0V$	600		V
$V_{GE(th)}$	$I_C = 250\mu\text{A}, V_{CE} = V_{GE}$	3.0		5.5 V
$I_{CES}$	$V_{CE} = V_{CES}, V_{GE} = 0V$ $T_J = 150^\circ\text{C}$			10 $\mu\text{A}$ 1 mA
$I_{GES}$	$V_{CE} = 0V, V_{GE} = \pm 20V$			$\pm 200$ nA
$V_{CE(sat)}$	$I_C = 150A, V_{GE} = 15V$ , Note 1 $T_J = 150^\circ\text{C}$		1.77 2.10	V V

Symbol Test Conditions ( $T_J = 25^\circ\text{C}$ Unless Otherwise Specified)		Characteristic Values		
		Min.	Typ.	Max.
$g_{fs}$	$I_C = 60\text{A}, V_{CE} = 10\text{V}$ , Note 1	40	70	S
$C_{ies}$	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$		6950	pF
$C_{oes}$			400	pF
$C_{res}$			150	pF
$Q_{g(on)}$	$I_C = 150\text{A}, V_{GE} = 15\text{V}, V_{CE} = 0.5 \cdot V_{CES}$		260	nC
$Q_{ge}$			39	nC
$Q_{gc}$			115	nC
$t_{d(on)}$	<b>Inductive load, <math>T_J = 25^\circ\text{C}</math></b> $I_C = 75\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 400\text{V}, R_G = 2\Omega$ Note 2		27	ns
$t_{ri}$			88	ns
$E_{on}$			4.20	mJ
$t_{d(off)}$			167	ns
$t_{fi}$			80	ns
$E_{off}$			2.60	mJ
$t_{d(on)}$	<b>Inductive load, <math>T_J = 150^\circ\text{C}</math></b> $I_C = 75\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 400\text{V}, R_G = 2\Omega$ Note 2		26	ns
$t_{ri}$			84	ns
$E_{on}$			5.30	mJ
$t_{d(off)}$			220	ns
$t_{fi}$			110	ns
$E_{off}$			3.76	mJ
$R_{thJC}$				0.18 $^\circ\text{C/W}$
$R_{thCS}$		0.05		$^\circ\text{C/W}$

**Notes:**

1. Pulse test,  $t \leq 300\mu\text{s}$ , duty cycle,  $d \leq 2\%$ .
2. Switching times & energy losses may increase for higher  $V_{CE}(\text{clamp})$ ,  $T_J$  or  $R_G$ .

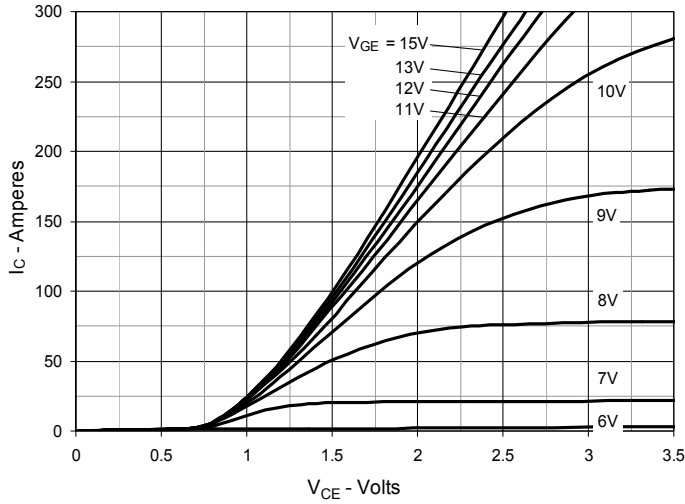
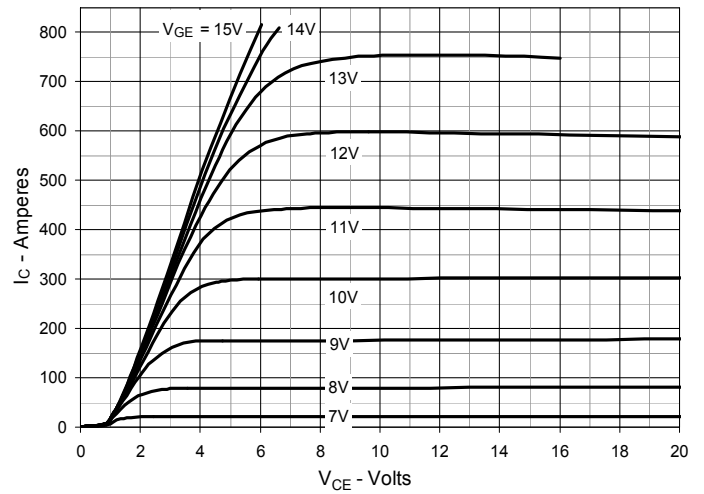
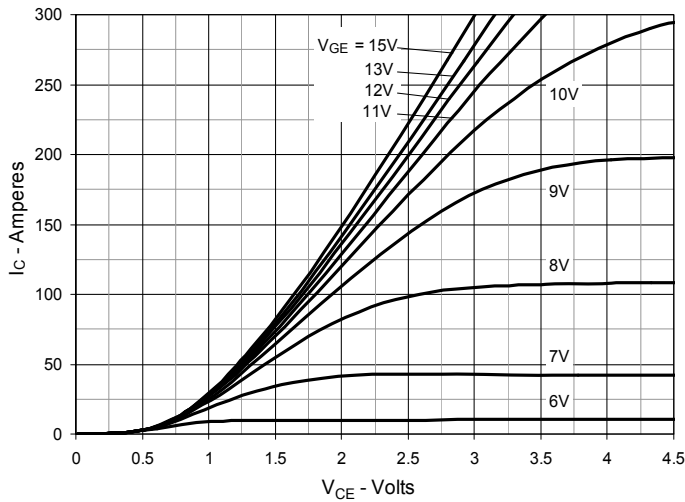
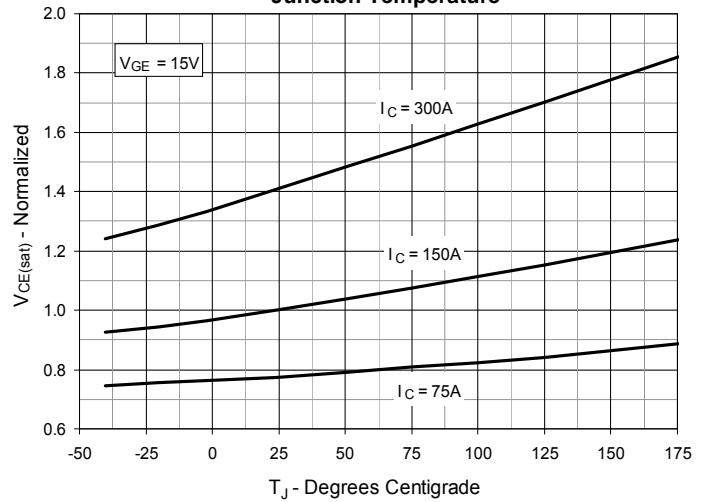
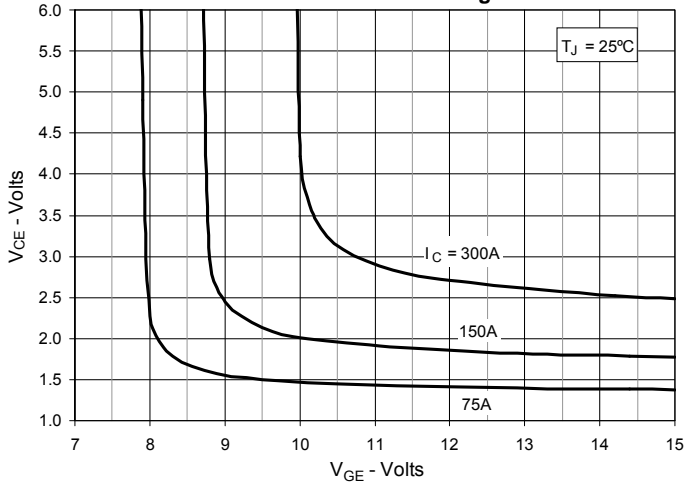
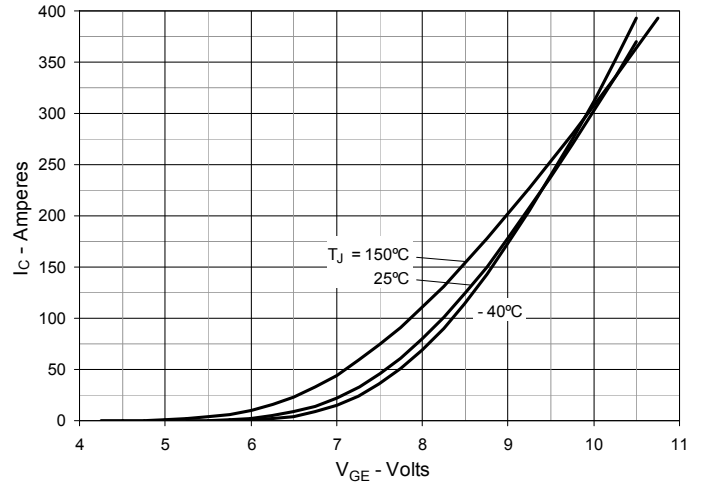


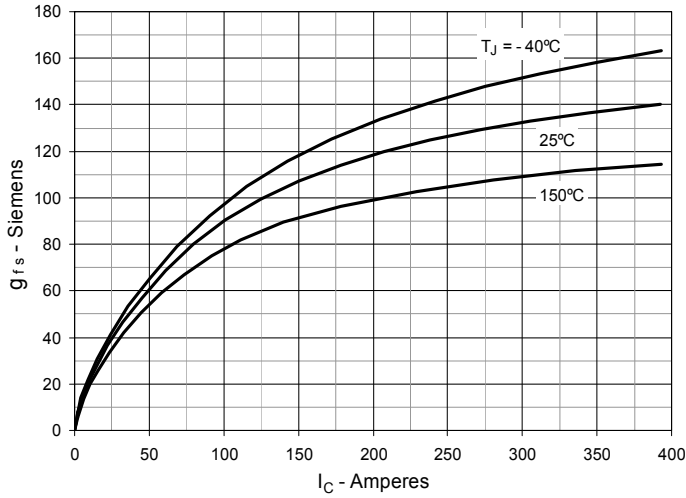
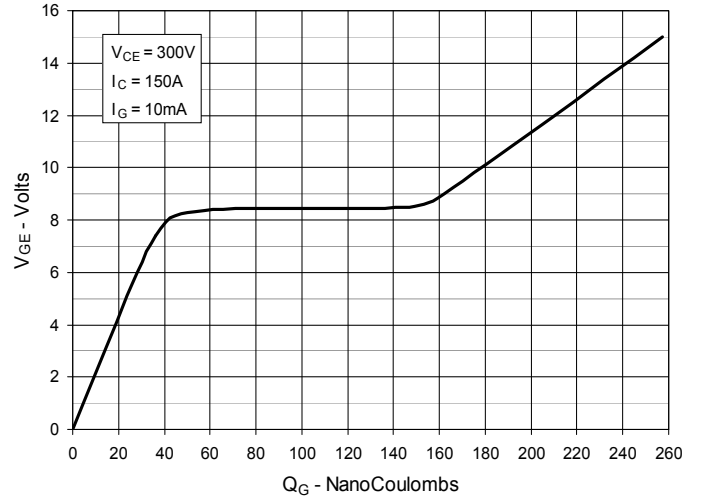
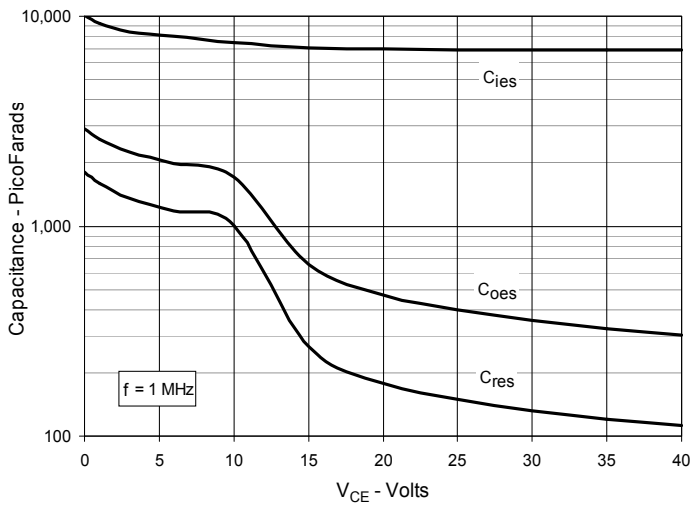
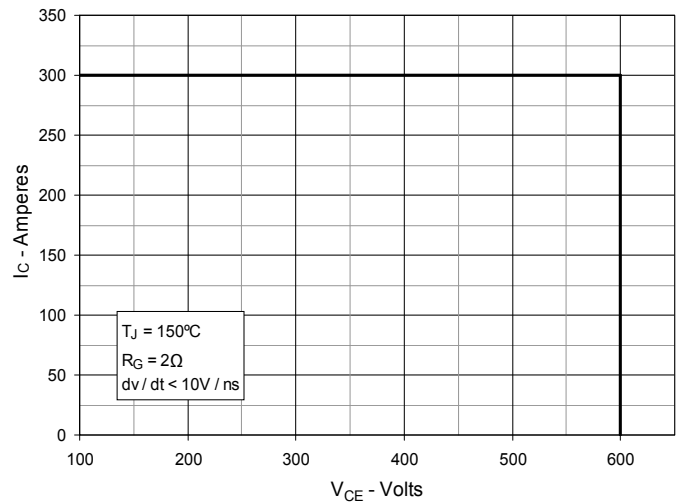
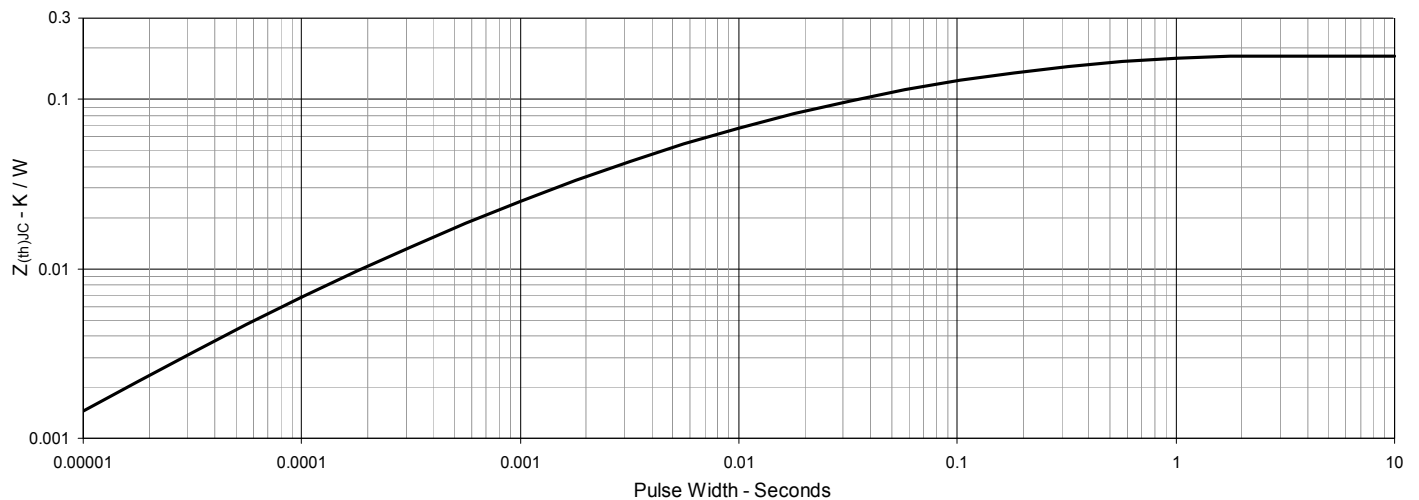
**PRELIMINARY TECHNICAL INFORMATION**

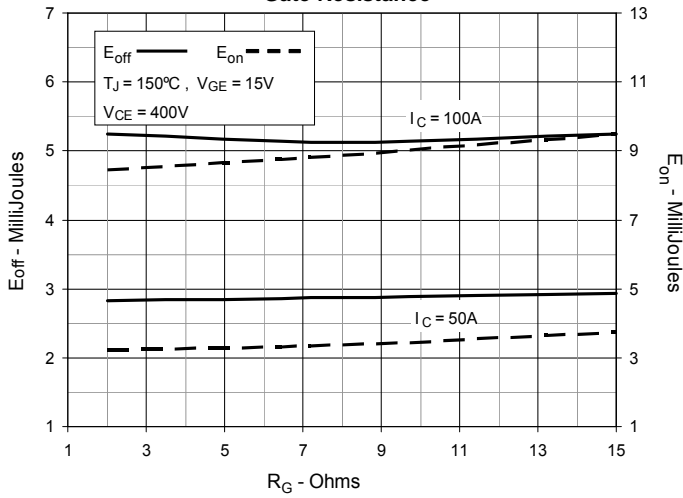
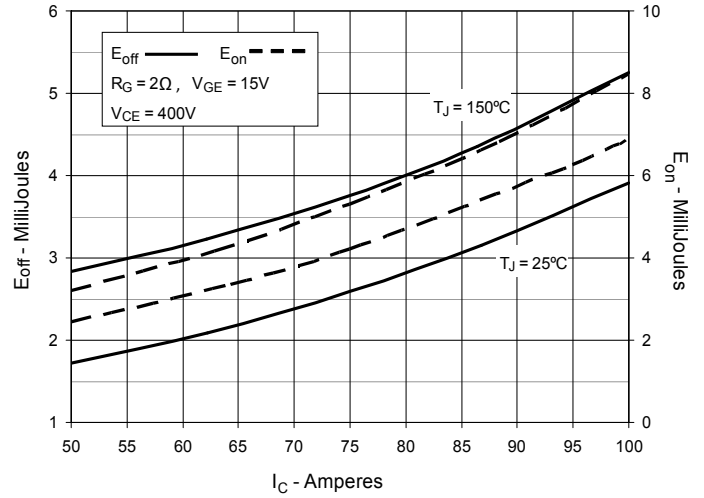
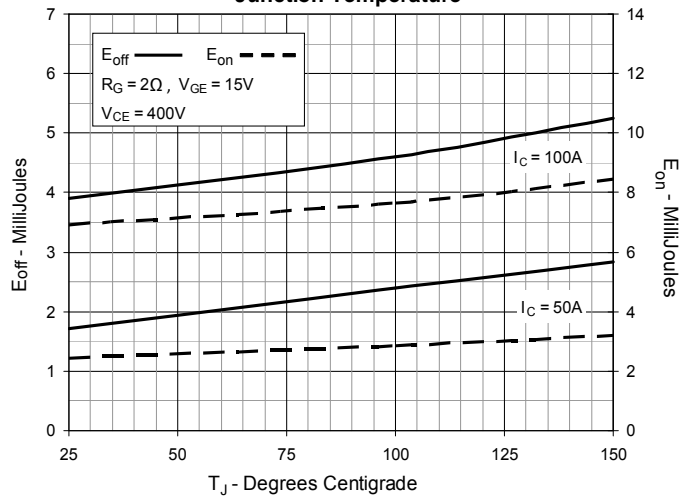
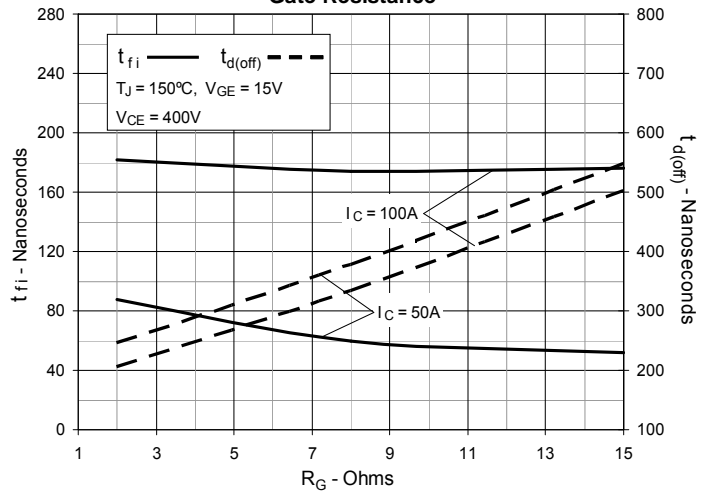
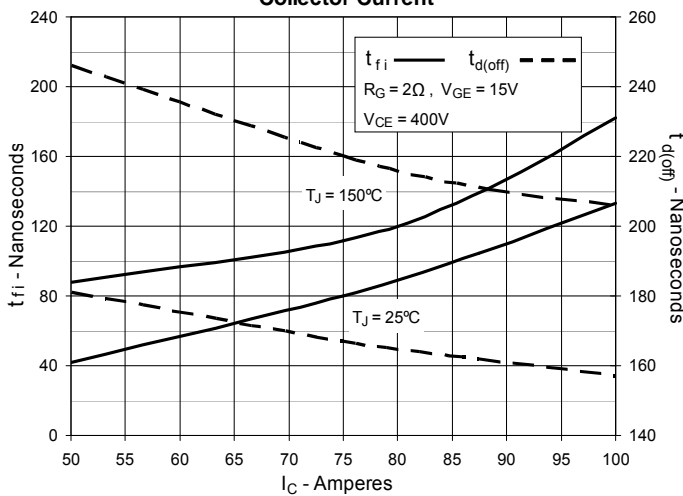
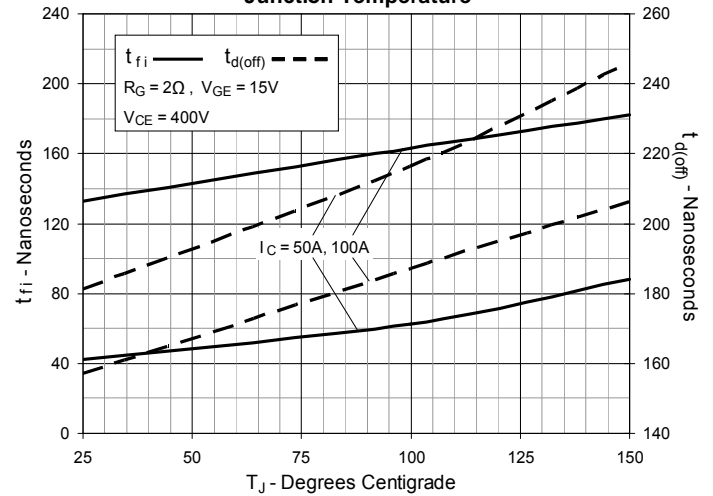
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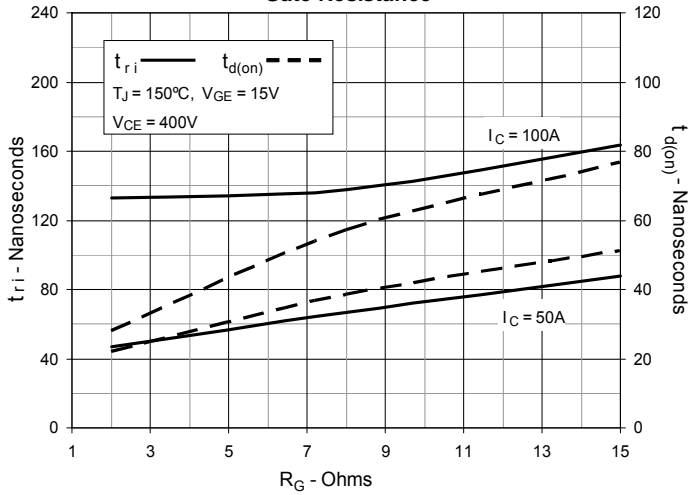
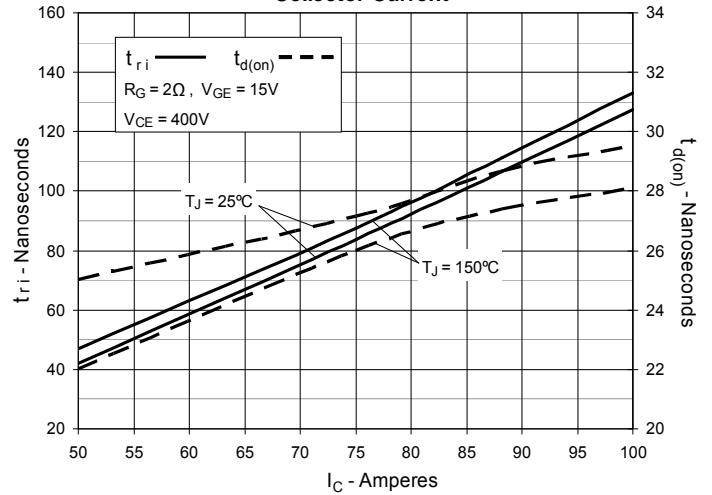
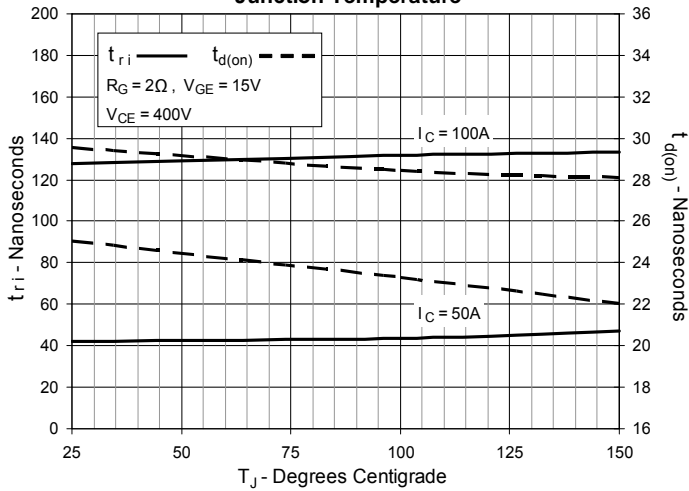
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	4,860,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

**Fig. 1. Output Characteristics @  $T_J = 25^\circ\text{C}$** 

**Fig. 2. Extended Output Characteristics @  $T_J = 25^\circ\text{C}$** 

**Fig. 3. Output Characteristics @  $T_J = 150^\circ\text{C}$** 

**Fig. 4. Dependence of  $V_{CE(sat)}$  on Junction Temperature**

**Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage**

**Fig. 6. Input Admittance**


**Fig. 7. Transconductance**

**Fig. 8. Gate Charge**

**Fig. 9. Capacitance**

**Fig. 10. Reverse-Bias Safe Operating Area**

**Fig. 11. Maximum Transient Thermal Impedance**


**Fig. 12. Inductive Switching Energy Loss vs. Gate Resistance**

**Fig. 13. Inductive Switching Energy Loss vs. Collector Current**

**Fig. 14. Inductive Switching Energy Loss vs. Junction Temperature**

**Fig. 15. Inductive Turn-off Switching Times vs. Gate Resistance**

**Fig. 16. Inductive Turn-off Switching Times vs. Collector Current**

**Fig. 17. Inductive Turn-off Switching Times vs. Junction Temperature**


**Fig. 18. Inductive Turn-on Switching Times vs. Gate Resistance**

**Fig. 19. Inductive Turn-on Switching Times vs. Collector Current**

**Fig. 20. Inductive Turn-on Switching Times vs. Junction Temperature**


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[XD25H120CX0](#) [XP15PJS120CL1B1](#) [IGW30N60H3FKSA1](#) [STGWA8M120DF3](#) [IGW08T120FKSA1](#) [IGW75N60H3FKSA1](#)  
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